



ZXTP56020FDBQ

20V DUAL PNP LOW V_{CE(SAT)} TRANSISTOR

Features

- BV_{CEO} > -20V
- I_C = -2A High Continuous Collector Current
- $R_{CE(SAT)} = 100 m\Omega$ for a Low Equivalent On-Resistance
- Low Saturation Voltage V_{CE(SAT)} < -150mV @ -1A
- Sidewall Tin Plating for Wettable Flanks in AOI
- P_D up to 2.47W for Power Demanding Applications
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

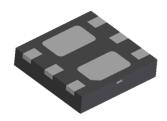
Mechanical Data

- Case: U-DFN2020-6 (SWP) (Type A) with Sidewall Plating (SWP)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin, Solderable per MIL-STD-202, Method 208 [®]
- Weight: 0.0065 grams (Approximate)

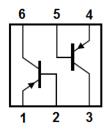
Application

- Matrix LED Lighting
- Power Management

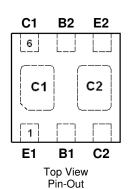
U-DFN2020-6 (SWP) (Type A)



Bottom View



Device Symbol



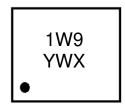
Ordering Information (Notes 4 & 5)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel	
ZXTP56020FDBQ-7	1W9	7	8	3,000	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1W9 = Product Type Marking Code Y = Year: 0~9

W = Week: A~Z: 1~26 week; a~z; 27~52 week; z represents

52 and 53 week X = A~Z: Internal Code



Absolute Maximum Ratings - Q1 & Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-2	Α
Peak Pulse Collector Current	I _{CM}	-3	A
Base Current	I _B	-300	mA
Peak Base Current	I _{BM}	-1	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 6 & 8)		405		
Power Dissipation	(Notes 6 & 9)	Ъ	510	mW	
rower dissipation	(Notes 7 & 8)	P _D	1650		
	(Notes 7 & 9)		2470		
	(Notes 6 & 8)		308		
Thermal Desistance, Junction to Ambient	(Notes 6 & 9)] _ [245	°C/W	
nermal Resistance, Junction to Ambient	(Notes 7 & 8)	$R_{\theta JA}$	76	°C/ VV	
	(Notes 7 & 9)		51		
Thermal Resistance, Junction to Lead	(Note 10)	$R_{ heta JL}$	18	°C/W	
Operating and Storage Temperature Range	_	T _{J,} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 11)

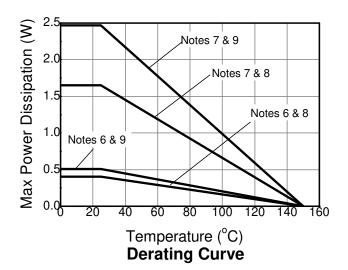
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

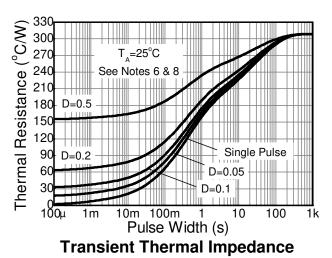
Notes:

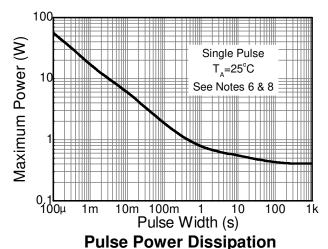
- 6. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR-4 PCB; device is For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a sing measured under still air conditions whilst operating in a steady-state.
 Same as note (6), except the device is mounted with the collector pad on 28mm x 28mm (8cm²) 2oz copper.
 For a dual device with one active die.
 For dual device with 2 active die running at equal power.
 Thermal resistance from junction to solder-point (on the exposed collector pads).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.

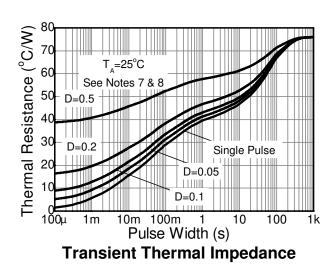


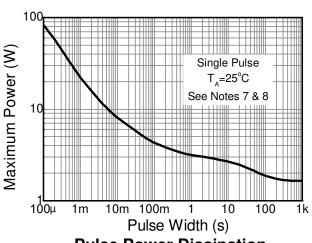
Thermal Characteristics and Derating Information











Pulse Power Dissipation



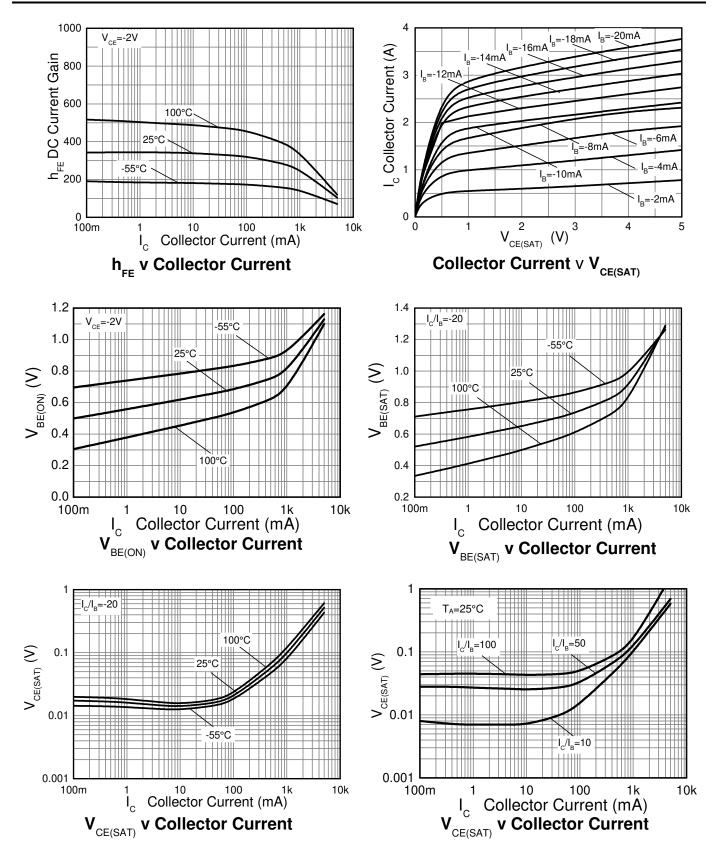
Electrical Characteristics – Q1 & Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CBO}	-20	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 12)		-20	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage		-7	_	_	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	1		_	-100	nA	$V_{CB} = -16V, I_{E} = 0$
	I _{CBO}		_	-50	μΑ	$V_{CB} = -16V$, $I_E = 0$, $T_A = +150$ °C
Emitter-Base Cutoff Current	I _{EBO}		_	-100	nA	$V_{EB} = -5.6V, I_{C} = 0$
		250	_	_		$V_{CE} = -2V, I_{C} = -100mA$
		210	_	_		$V_{CE} = -2V, I_{C} = -500mA$
DC Current Gain (Note 12)	hFE	170	_	_	_	$V_{CE} = -2V, I_{C} = -700mA$
		160	_	_		$V_{CE} = -2V, I_{C} = -1A$
		100	_	_		$V_{CE} = -2V, I_{C} = -2A$
	V _{CE(SAT)}	_	_	-110		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
			_	-220	mV	$I_C = -1A$, $I_B = -50mA$
Collector-Emitter Saturation Voltage (Note 12)			_	-200		$I_C = -0.7A$, $I_B = -7mA$
		_	_	-390		$I_C = -2A$, $I_B = -200mA$
Equivalent On-Resistance (Note 12)	R _{CE(SAT)}		_	220	mΩ	$I_E = -1A$, $I_B = -50mA$
		_	_	-1		$I_C = -0.5A$, $I_B = -50mA$
Base-Emitter Saturation Voltage (Note 12)	$V_{BE(SAT)}$	_	_	-1.1	V	$I_C = -1A, I_B = -50mA$
	, ,	_	_	-1.25		I _C = -2A, I _B = -200mA
Base-Emitter Turn-on Voltage (Note 12)	V _{BE(ON)}			-0.9	V	$V_{CE} = -2V, I_{C} = -0.5A$
Turn-On Time Delay Time Rise Time			60	_	ns	
			10	_	ns	$I_C = -1A$, $I_{B1} = -I_{B2} = 50$ mA;
		_	50	_	ns	T _A = +25°C

Note: 12. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

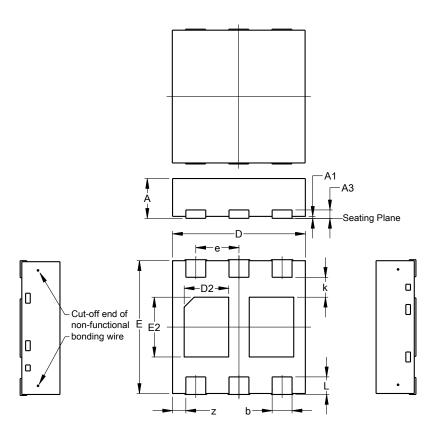




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (SWP) (Type A)

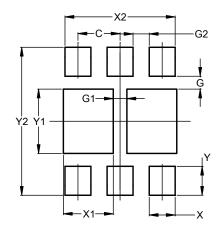


U-DFN2020-6 (SWP)						
(Type A)						
Dim	Min	Max	Тур			
Α	0.55	0.65	0.60			
A1	0.00	0.05	0.03			
A3			0.127			
b	0.25	0.35	0.30			
D	1.95	2.05	2.00			
D2	D2 0.57		0.67			
Е	1.95	2.05	2.00			
E2	0.80 1.00 0.90					
е	e 0.65BSC					
k	0.30BSC					
L	0.22	0.32	0.27			
Z	0.20BSC					
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (SWP) (Type A)



Dimensions	Value
Dilliensions	(in mm)
С	0.650
G	0.200
G1	0.210
G2	0.250
X	0.400
X1	0.770
X2	1.700
Υ	0.450
Y1	1.000
Y2	2.300

April 2017

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